### IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Tikashi AKATSU et al.

Application No:

Group Art Unit:

Filing Date: Concurrently herewith

Examiner:

WAFER WITH A RELAXED USEFUL LAYER AND METHOD OF FORMING THE

WAFER

Attorney Docket No.: 4717-8900

## INFORMATION DISCLOSURE STATEMENT

### MS PATENT APPLICATION

Commissioner for Patents P.O. Box 1450 Arlexandria, Virginia 22313-1450

Sept. 17, 2003

Sir:

Pursuant to Applicant's duty of disclosure under 37 C.F.R. § 1.56, enclosed are copies of Nine (9) references listed on the enclosed Form PTO-1449 for the Examiner's review. Also enclosed is a copy of the International Search Report from the corresponding foreign application on which the references were cited.

It is respectfully requested that the references be made of record in this application by the Examiner's completion and return of the attached Form PTO-1449.

No fee is believed to be due for the submission of the references. Should any fees be required, however, please charge such fees to Winston & Strawn Deposit Account No. 50-1814. A copy of this sheet is enclosed for accounting purposes.

Respectfully submitted,

E. Bradley Gould For: Allan A. Fanucci (Reg. No. 41,792) (Reg. No. 30,256)

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202-371-5771

# LIST OF REFERENCES CITED BY APPLICANT Form PTO-1449

(Use several sheets if necessary)

| ATTY. DOCKET NO.:      | APPLICATION NO.: |  |
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| APPLICANT:             |                  |  |
| Tukeshi AKATSU, et al. |                  |  |
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Sheet 1 of 1

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|                      |             |                    | U.S. PAT | ENT DOCUMENTS       |          |          |          |         |
|----------------------|-------------|--------------------|----------|---------------------|----------|----------|----------|---------|
| *EXAMINER<br>INITIAL | CITE<br>NO. | DOCUMENT NUMBER    | DATE     | Name                | CLASS    | SUBCLASS | FILING I | DATE IF |
|                      |             | US 2002/0185686 A1 | 12/2002  | Christiansen et al. | 257      | 347      |          |         |
|                      |             | US 2002/0072130 A1 | 06/2002  | Cheng et al.        | 438      | 10       |          |         |
|                      |             | US 2001/0003269    | 06/2001  | Wu et al.           | 117      | 94       |          |         |
|                      |             | 6,064,081          | 05/2000  | Robinson            | 257      | 183      |          |         |
|                      |             | 5,461,243          | 10/1995  | Ek et al.           | 257      | 190      |          |         |
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|                      |             |                    | FOREIGN  | PATENT DOCUMENTS    |          |          |          |         |
|                      |             | DOCUMENT NUMBER    | DATE     | COUNTRY             | CLASS    | SUBCLASS | TRANSL   |         |
|                      | <u> </u>    |                    |          |                     | <u> </u> | ļ        | YES      | NO      |
|                      | <u> </u>    | EP 0 849 788 A     | 06/1998  | Europe              | ļ        | ļ        |          |         |
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## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

- H. Trinkaus, Strain relaxation mechanism for hydrogen-implanted Si<sub>1-x</sub>Ge<sub>x</sub>/Si(100) heterostructures, 12 June 2000, pp. 3552-54.
- B. Holländer, Strain relaxation of pseudomorphic  $Si_{1x}$ Ge<sub>x</sub>/Si(100) heterostructures after hydrogen or helium ion implantation for virtual substrate fabrication, 2001, pp. 357-67.
- B. Holländer, Substrate Engineering by Hydrogen or Helium Implantation for Epitaxial Growth of Lattice Mismatched Si<sub>1-x</sub>Ge<sub>x</sub> Films on Silicon, 2000, pp. 326-29.

### EXAMINER

DATE CONSIDERED

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.